

# Comlinear<sup>®</sup> CLC1003 Low Distortion, Low Offset, RRIO Amplifier

#### FEATURES

- 1mV max input offset voltage
- 0.00005% THD at 1kHz
- 5.3 nV/ $\sqrt{Hz}$  input voltage noise >10kHz
- -90dB/-85dB HD2/HD3 at 100kHz, R<sub>L</sub>=100Ω
- <-100dB HD2 and HD3 at 10kHz,  $R_L=1k\Omega$
- Rail-to-Rail input and output
- 55MHz unity gain bandwidth
- 12V/µs slew rate
- +80mA, -55mA output current
- -40°C to +125°C operating temperature range
- Fully specified at 3V and ±5V supplies
- CLC1003: Pb-free SOT23-5, SOIC-8
- Future option CLC2003: Dual
- Future option CLC4003: Quad

#### APPLICATIONS

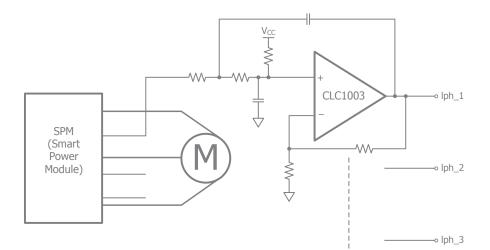
- Active filters
- Sensor interface
- High-speed transducer amp
- Medical instrumentation
- Probe equipment
- Test equipment
- Smoke detecters
- Hand-held analytic instruments

### General Description

The COMLINEAR CLC1003 is a single channel, high-performance, voltage feedback amplifier with near precision performance, low input voltage noise, and ultra low distortion. The CLC1003 family of amplifiers offers 1mV maximum input offset voltage, 3.5nV/ $\sqrt{Hz}$  broadband input voltage noise, and 0.00005% THD at 1kHz. These amplifiers also provide 55MHz gain bandwidth product and 12V/µs slew rate making them well suited for applications requiring precision DC performance and high AC performance. These COMLINEAR high-performance amplifiers also offer a rail-to-rail input and output, simplifying single supply designs and offering larger dynamic range possibilities. The inputs extend beyond the rails by 500mV.

The COMLINEAR CLC1003 family of amplifiers are designed to operate from 2.5V to 12V supplies and operate over the extended temperature range of  $-40^{\circ}$ C to  $+125^{\circ}$ .

### Typical Application - Current Sensing in 3-Phase Motor



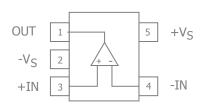
### Ordering Information

Part Number	Package	Pb-Free	RoHS Compliant	Operating Temperature Range	Packaging Method
CLC1003IST5X	SOT23-5	Yes	Yes	-40°C to +85°C	Reel
CLC1003ISO8X*	SOIC-8	Yes	Yes	-40°C to +85°C	Reel
CLC1003ISO8*	SOIC-8	Yes	Yes	-40°C to +85°C	Rail
CLC1003AST5X	SOT23-5	Yes	Yes	-40°C to +125°C	Reel
CLC1003ASO8X*	SOIC-8	Yes	Yes	-40°C to +125°C	Reel
CLC1003ASO8*	SOIC-8	Yes	Yes	-40°C to +125°C	Rail

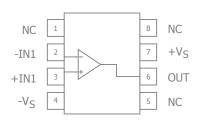
\*Preliminary Product Information

Moisture sensitivity level for all parts is MSL-1.

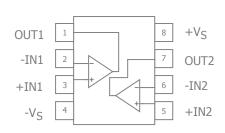
# CLC1003 SOT Pin Configuration



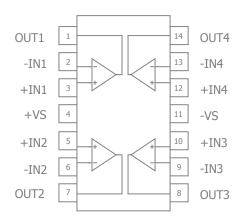
## CLC1003 SOIC Pin Configuration



# CLC2003 Pin Configuration



# CLC4003 Pin Configuration



### CLC1003 SOT23-5 Pin Assignments

Pin No.	Pin Name	Description
1	OUT	Output
2	-V <sub>S</sub>	Negative supply
3	+IN	Positive input
4	-IN	Negative input
5	+V <sub>S</sub>	Positive supply

### CLC1003 SOIC Pin Assignments

Pin No.	Pin Name	Description
1	NC	No connect
2	-IN1	Negative input
3	+IN1	Positive input
4	-V <sub>S</sub>	Negative supply
5	NC	No connect
6	OUT	Output
7	+V <sub>S</sub>	Positive supply
8	NC	No connect

# CLC2003 (Future Option) Pin Configuration

Pin No.	Pin Name	Description
1	OUT1	Output, channel 1
2	-IN1	Negative input, channel 1
3	+IN1	Positive input, channel 1
4	-V <sub>S</sub>	Negative supply
5	+IN2	Positive input, channel 2
6	-IN2	Negative input, channel 2
7	OUT2	Output, channel 2
8	+V <sub>S</sub>	Positive supply

### CLC4003 (Future Option) Pin Configuration

Pin No.	Pin Name	Description
1	OUT1	Output, channel 1
2	-IN1	Negative input, channel 1
3	+IN1	Positive input, channel 1
4	+Vs	Positive supply
5	+IN2	Positive input, channel 2
6	-IN2	Negative input, channel 2
7	OUT2	Output, channel 2
8	OUT3	Output, channel 3
9	-IN3	Negative input, channel 3
10	+IN3	Positive input, channel 3
11	-V <sub>S</sub>	Negative supply
12	+IN4	Positive input, channel 4
13	-IN4	Negative input, channel 4
14	OUT4	Output, channel 4

#### Absolute Maximum Ratings

The safety of the device is not guaranteed when it is operated above the "Absolute Maximum Ratings". The device should not be operated at these "absolute" limits. Adhere to the "Recommended Operating Conditions" for proper device function. The information contained in the Electrical Characteristics tables and Typical Performance plots reflect the operating conditions noted on the tables and plots.

Parameter	Min	Max	Unit
Supply Voltage	0	14	V
Input Voltage Range	-V <sub>s</sub> -0.5V	+V <sub>s</sub> +0.5V	V

#### **Reliability Information**

Parameter	Min	Тур	Max	Unit
Junction Temperature			150	°C
Storage Temperature Range	-65		150	°C
Lead Temperature (Soldering, 10s)			260	°C
Package Thermal Resistance				
5-Lead SOT23		221		°C/W
8-Lead SOIC		100		°C/W
14-Lead SOIC		88		°C/W

Notes:

Package thermal resistance ( $\theta_{\text{JA}}$ ), JDEC standard, multi-layer test boards, still air.

#### **Recommended Operating Conditions**

Parameter	Min	Тур	Max	Unit
Operating Temperature Range (CLC1003I)	-40		+85	°C
Operating Temperature Range (CLC1003A)	-40		+125	°C
Supply Voltage Range	2.5		12	V

### Electrical Characteristics at +3V

 $T_A$  = 25°C,  $V_s$  = +3V,  $R_f$  = 1k\Omega,  $R_L$  = 1k\Omega to  $V_S/2,$  G = 2; unless otherwise noted.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
Frequency D	Domain Response			,		
GBWP	-3dB Gain Bandwidth Product	$G = 10, V_{OUT} = 0.05V_{pp}$		31		MHz
UGBW	Unity Gain Bandwidth	$V_{OUT} = 0.05 V_{pp}$ , $R_f = 0$		50		MHz
BW <sub>SS</sub>	-3dB Bandwidth	$V_{OUT} = 0.05 V_{pp}$		24		MHz
BW <sub>LS</sub>	Large Signal Bandwidth	$V_{OUT} = 2V_{pp}$		3.3		MHz
Time Domai	n Response					
t <sub>R</sub> , t <sub>F</sub>	Rise and Fall Time	V <sub>OUT</sub> = 2V step; (10% to 90%)		150		ns
ts	Settling Time to 0.1%	V <sub>OUT</sub> = 2V step		78		ns
OS	Overshoot	V <sub>OUT</sub> = 2V step		0.3		%
SR	Slew Rate	2V step		11		V/µs
Distortion/N	loise Response					
		$2V_{pp}$ , 10kHz, $R_L = 1k\Omega$		-98		dBc
HD2	2nd Harmonic Distortion	$2V_{pp'}$ 100kHz, R <sub>L</sub> = 100 $\Omega$		-85		dBc
		$2V_{pp}$ , 10kHz, $R_L = 1k\Omega$		-95		dBc
HD3	3rd Harmonic Distortion	$2V_{pp'}$ 100kHz, R <sub>L</sub> = 100 $\Omega$		-81		dBc
THD	Total Harmonic Distortion	$1V_{pp}$ , 1kHz, G=1, R <sub>L</sub> = 2kΩ		0.0005		%
		> 10kHz		5.5		nV/√Hz
e <sub>n</sub>	e <sub>n</sub> Input Voltage Noise	> 100kHz		3.9		nV/√Hz
DC Performa	ance					
V <sub>IO</sub>	Input Offset Voltage			0.088		mV
dV <sub>IO</sub>	Average Drift			1.3		μV/°C
I <sub>b</sub>	Input Bias Current			-0.340		μA
dI <sub>b</sub>	Average Drift			0.8		nA/°C
I <sub>os</sub>	Input Offset Current			0.2		nA
PSRR	Power Supply Rejection Ratio	DC		100		dB
A <sub>OL</sub>	Open-Loop Gain	$V_{OUT} = V_S / 2$		104		dB
I <sub>S</sub>	Supply Current	per channel		1.85		mA
Input Chara	cteristics			,		
R <sub>IN</sub>	Input Resistance	Non-inverting, G = 1		30		MΩ
C <sub>IN</sub>	Input Capacitance			1.1		pF
CMIR	Common Mode Input Range			-0.5 to 3.5		V
CMRR	Common Mode Rejection Ratio	DC , V <sub>cm</sub> =0.5V to 2.5V		94		dB
Output Char		er dit er er er				
				0.085 to		
V <sub>OUT</sub>	Output Voltage Swing	$R_{L} = 150\Omega$		2.80		V
- 001	v <sub>OUT</sub> Output voitage Swilig	$R_L = 1k\Omega$		0.04 to 2.91		V
I <sub>OUT</sub>	Output Current			+75, -40		mA
I <sub>SC</sub>	Short-Circuit Output Current	$V_{OUT} = V_S / 2$		+95, -50		mA

#### Notes:

1. 100% tested at 25°C

### Electrical Characteristics at ±5V

 $T_A$  = 25°C,  $V_s$  = ±5V,  $R_f$  = 1k $\Omega,$   $R_L$  = 1k $\Omega$  to GND, G = 2; unless otherwise noted.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
Frequency D	Domain Response					
GBWP	-3dB Gain Bandwidth Product	$G = 10, V_{OUT} = 0.05V_{pp}$		35		MHz
UGBW	Unity Gain Bandwidth	$V_{OUT} = 0.05V_{pp}, R_f = 0$		55		MHz
BW <sub>SS</sub>	-3dB Bandwidth	$V_{OUT} = 0.05V_{pp}$		25		MHz
BW <sub>LS</sub>	Large Signal Bandwidth	$V_{OUT} = 2V_{pp}$		3.6		MHz
Time Domai	in Response		ł			
t <sub>R</sub> , t <sub>F</sub>	Rise and Fall Time	V <sub>OUT</sub> = 2V step; (10% to 90%)		125		ns
ts	Settling Time to 0.1%	V <sub>OUT</sub> = 2V step		80		ns
OS	Overshoot	V <sub>OUT</sub> = 2V step		0.3		%
SR	Slew Rate	4V step		12		V/µs
Distortion/N	loise Response		I	1		1
		$2V_{pp'}$ 10kHz, R <sub>L</sub> = 1k $\Omega$		-125		dBc
HD2	2nd Harmonic Distortion	$2V_{pp}$ , 100kHz, R <sub>L</sub> = 100 $\Omega$		-90		dBc
		$2V_{pp}$ , 10kHz, $R_L = 1k\Omega$		-127		dBc
HD3	3rd Harmonic Distortion	$2V_{pp}$ , 100kHz, R <sub>L</sub> = 100 $\Omega$		-85		dBc
THD	Total Harmonic Distortion	$1V_{pp}$ , 1kHz, G=1, R <sub>L</sub> = 2k $\Omega$		0.00005		%
		> 10kHz		5.3		nV/√Hz
e <sub>n</sub>	Input Voltage Noise	> 100kHz		3.5		nV/√Hz
DC Performa	ance	l.	I			1
V <sub>IO</sub>	Input Offset Voltage <sup>(1)</sup>		-1	0.050	1	mV
dV <sub>IO</sub>	Average Drift			1.3		μV/°C
I <sub>b</sub>	Input Bias Current (1)		-2.6	-0.30	2.6	μA
dI <sub>b</sub>	Average Drift			0.85		nA/°C
I <sub>os</sub>	Input Offset Current (1)			0.2	0.7	μA
PSRR	Power Supply Rejection Ratio (1)	DC	82	100		dB
A <sub>OL</sub>	Open-Loop Gain (1)	$V_{OUT} = V_S / 2$	95	115		dB
I <sub>S</sub>	Supply Current (1)	per channel		2.2	2.75	mA
Input Chara	cteristics					
R <sub>IN</sub>	Input Resistance	Non-inverting, G = 1		30		MΩ
C <sub>IN</sub>	Input Capacitance			1		pF
CMIR	Common Mode Input Range			±5.5		V
CMRR	Common Mode Rejection Ratio (1)	DC , V <sub>cm</sub> = -3V to 3V	70	95		dB
Output Char	racteristics		I			
		$R_L = 150\Omega$		-4.826 to 4.534		V
V <sub>OUT</sub>	Output Voltage Swing	$R_{L} = 1k\Omega^{(1)}$	-4.7	-4.93 to 4.85	4.7	V
I <sub>OUT</sub>	Output Current			+80, -55		mA
I <sub>SC</sub>	Short-Circuit Output Current	$V_{OUT} = V_S / 2$		+115, -90		mA

#### Notes:

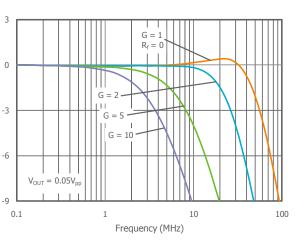
1. 100% tested at 25°C

Normalized Gain (dB)

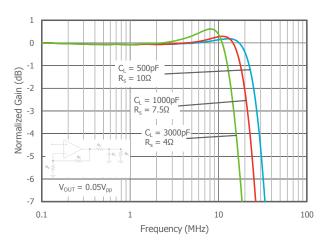
#### Typical Performance Characteristics

 $T_A$  = 25°C,  $V_s$  = ±5V,  $R_f$  = 1k $\Omega,$   $R_L$  = 1k $\Omega$  to GND, G = 2; unless otherwise noted.

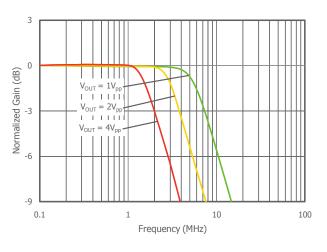
Non-Inverting Frequency Response



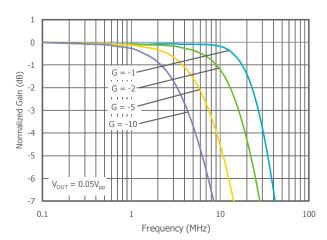
Frequency Response vs. CL



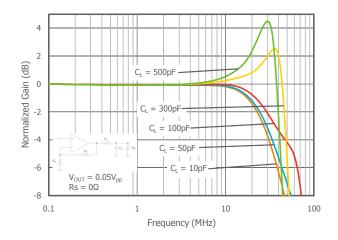




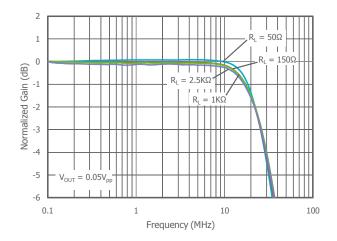
Inverting Frequency Response



Frequency Response vs. C<sub>L</sub> without R<sub>S</sub>



Frequency Response vs. R<sub>L</sub>

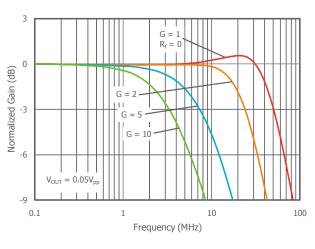


#### Typical Performance Characteristics

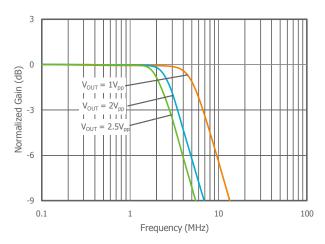
 $T_A = 25^{\circ}C$ ,  $V_s = \pm 5V$ ,  $R_f = 1k\Omega$ ,  $R_L = 1k\Omega$  to GND, G = 2; unless otherwise noted.

Non-Inverting Frequency Response at  $V_S = 3V$ 

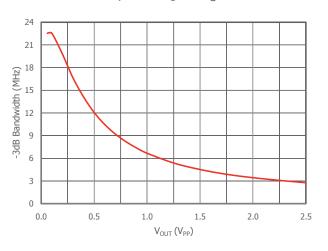


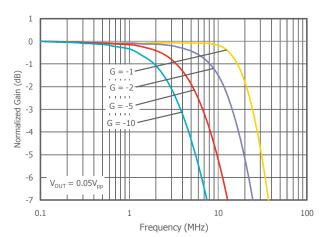


Frequency Response vs.  $V_{OUT}$  at  $V_S = 3V$ 

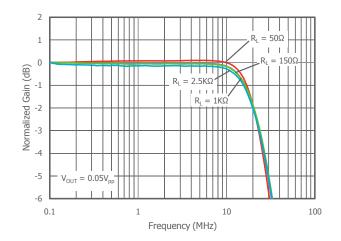


-3dB Bandwidth vs. Output Voltage at  $V_S = 3V$ 

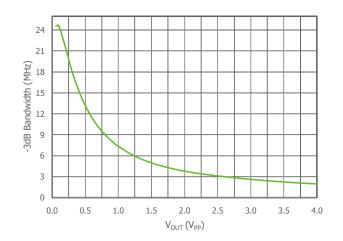




Frequency Response vs.  $R_L$  at  $V_S = 3V$ 

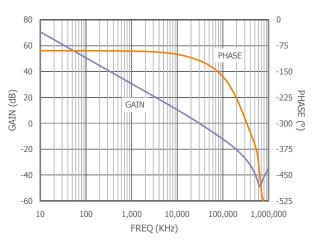


-3dB Bandwidth vs. Output Voltage

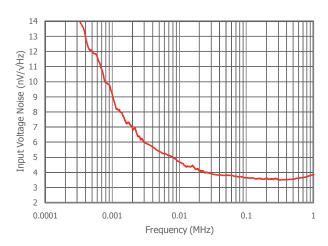


 $T_A$  = 25°C,  $V_s$  = ±5V,  $R_f$  = 1k $\Omega,$   $R_L$  = 1k $\Omega$  to GND, G = 2; unless otherwise noted.

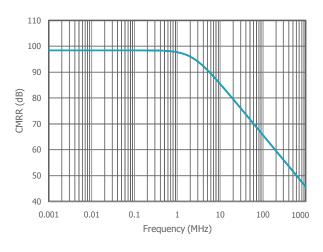
Open Loop Gain and Phase vs. Frequency



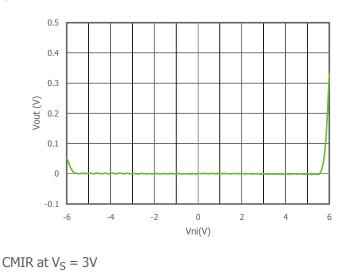
Input Voltage Noise

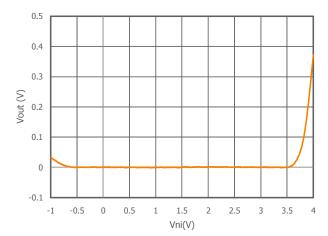




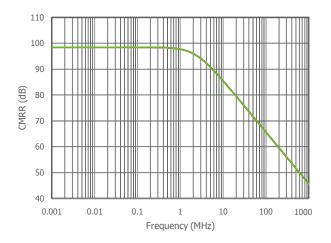


CMIR



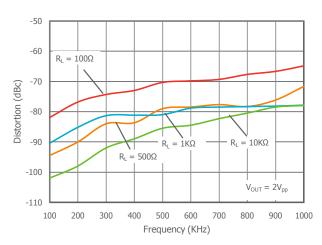


PSRR vs. Frequency

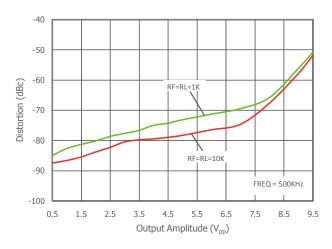


 $T_A = 25^{\circ}C$ ,  $V_s = \pm 5V$ ,  $R_f = 1k\Omega$ ,  $R_L = 1k\Omega$  to GND, G = 2; unless otherwise noted.

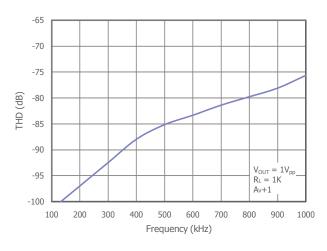
2nd Harmonic Distortion vs. RL



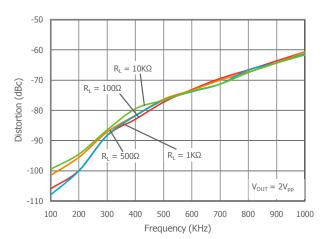
2nd Harmonic Distortion vs.  $V_{OUT}$ 



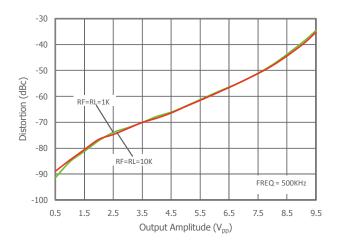
THD vs. Frequency



3rd Harmonic Distortion vs. R<sub>L</sub>

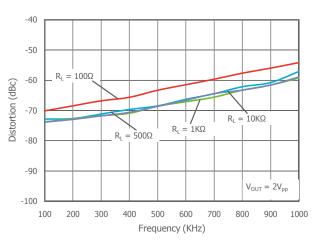


3rd Harmonic Distortion vs.  $V_{OUT}$ 

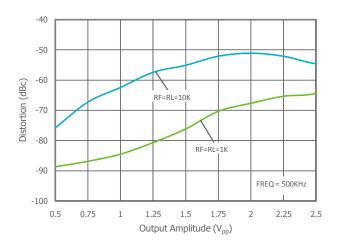


 $T_A$  = 25°C,  $V_s$  = ±5V,  $R_f$  = 1k $\Omega,$   $R_L$  = 1k $\Omega$  to GND, G = 2; unless otherwise noted.

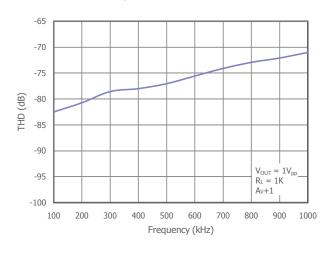
2nd Harmonic Distortion vs.  $R_L$  at  $V_S = 3V$ 



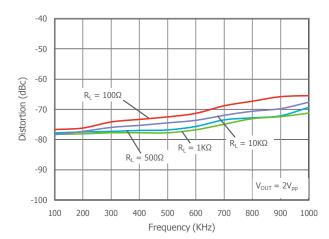




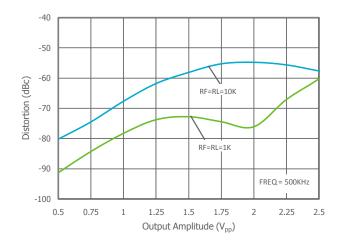
THD vs. Frequency at  $V_S = 3V$ 





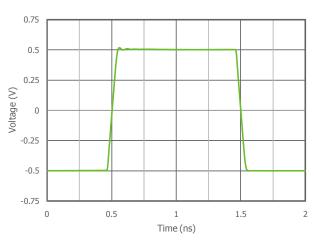


3rd Harmonic Distortion vs.  $V_{OUT}$  at  $V_S = 3V$ 

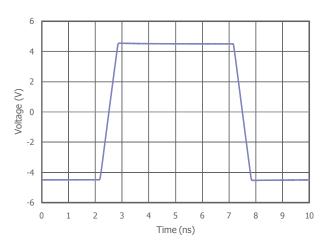


 $T_A = 25^{\circ}C$ ,  $V_s = \pm 5V$ ,  $R_f = 1k\Omega$ ,  $R_L = 1k\Omega$  to GND, G = 2; unless otherwise noted.

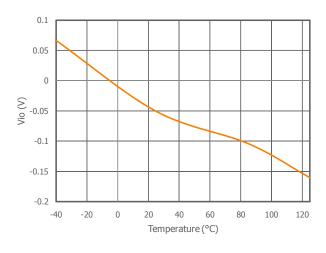
Small Signal Pulse Response



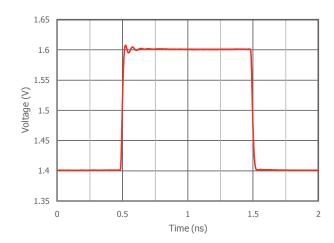
Large Signal Pulse Response



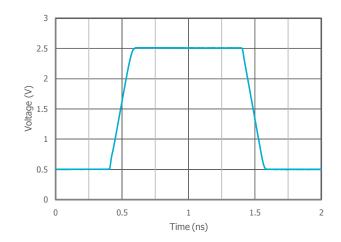




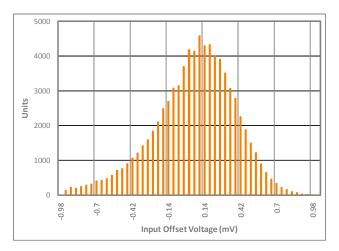
Small Signal Pulse Response at  $V_S = 3V$ 



Large Signal Pulse Response at  $V_S = 3V$ 



Input Offset Voltage Distribution



### **Application Information**

#### **Basic Operation**

Figures 1 and 2 illustrate typical circuit configurations for non-inverting, inverting, and unity gain topologies for dual supply applications. They show the recommended bypass capacitor values and overall closed loop gain equations.

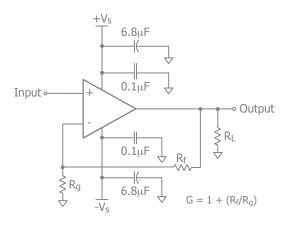


Figure 1. Typical Non-Inverting Gain Circuit

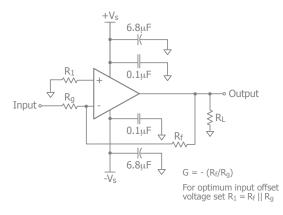


Figure 2. Typical Inverting Gain Circuit

#### Power Dissipation

Power dissipation should not be a factor when operating under the stated 300 ohm load condition. However, applications with low impedance, DC coupled loads should be analyzed to ensure that maximum allowed junction temperature is not exceeded. Guidelines listed below can be used to verify that the particular application will not cause the device to operate beyond it's intended operating range.

Maximum power levels are set by the absolute maximum junction rating of 150°C. To calculate the junction tem-

perature, the package thermal resistance value Theta<sub>JA</sub> ( $\Theta_{JA}$ ) is used along with the total die power dissipation.

 $T_{Junction} = T_{Ambient} + (\Theta_{JA} \times P_D)$ 

Where  $T_{\text{Ambient}}$  is the temperature of the working environment.

In order to determine  $P_D$ , the power dissipated in the load needs to be subtracted from the total power delivered by the supplies.

$$P_D = P_{supply} - P_{load}$$

Supply power is calculated by the standard power equation.

 $P_{supply} = V_{supply} \times I_{RMS \ supply}$ 

 $V_{supply} = V_{S+} - V_{S-}$ 

Power delivered to a purely resistive load is:

 $P_{load} = ((V_{LOAD})_{RMS^2})/Rload_{eff}$ 

The effective load resistor ( $Rload_{eff}$ ) will need to include the effect of the feedback network. For instance,

Rload<sub>eff</sub> in figure 3 would be calculated as:

 $R_L \parallel (R_f + R_q)$ 

These measurements are basic and are relatively easy to perform with standard lab equipment. For design purposes however, prior knowledge of actual signal levels and load impedance is needed to determine the dissipated power. Here,  $P_D$  can be found from

 $P_D = P_{Quiescent} + P_{Dynamic} - P_{Load}$ 

Quiescent power can be derived from the specified  $\rm I_S$  values along with known supply voltage,  $\rm V_{Supply}.$  Load power can be calculated as above with the desired signal amplitudes using:

 $(V_{LOAD})_{RMS} = V_{PEAK} / \sqrt{2}$ 

 $(I_{LOAD})_{RMS} = (V_{LOAD})_{RMS} / Rload_{eff}$ 

The dynamic power is focused primarily within the output stage driving the load. This value can be calculated as:

 $P_{DYNAMIC} = (V_{S+} - V_{LOAD})_{RMS} \times (I_{LOAD})_{RMS}$ 

Assuming the load is referenced in the middle of the power rails or  $V_{supply}/2$ .

Figure 3 shows the maximum safe power dissipation in the package vs. the ambient temperature for the packages available.

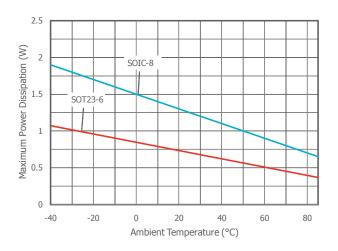


Figure 3. Maximum Power Derating

#### Driving Capacitive Loads

Increased phase delay at the output due to capacitive loading can cause ringing, peaking in the frequency response, and possible unstable behavior. Use a series resistance,  $R_S$ , between the amplifier and the load to help improve stability and settling performance. Refer to Figure 4.

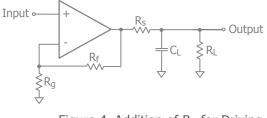


Figure 4. Addition of R<sub>S</sub> for Driving Capacitive Loads

The CLC1003 family of amplifiers is capable of driving up to 300pF directly, with no series resistance. Directly driving 500pF causes over 4dB of frequency peaking, as shown in the plot on page 6. Table 1 provides the recommended  $R_S$  for various capacitive loads. The recommended  $R_S$  values result in <=1dB peaking in the frequency response. The Frequency Response vs.  $C_L$  plots, on page 6, illustrates the response of the CLCx003.

C <sub>L</sub> (pF)	R <sub>S</sub> (Ω)	-3dB BW (MHz)
500	10	27
1000	7.5	20
3000	4	15

Table 1: Recommended  $R_S$  vs.  $C_L$ 

For a given load capacitance, adjust  $R_S$  to optimize the tradeoff between settling time and bandwidth. In general, reducing  $R_S$  will increase bandwidth at the expense of additional overshoot and ringing.

#### **Overdrive Recovery**

An overdrive condition is defined as the point when either one of the inputs or the output exceed their specified voltage range. Overdrive recovery is the time needed for the amplifier to return to its normal or linear operating point. The recovery time varies, based on whether the input or output is overdriven and by how much the range is exceeded. The CLCx003 will typically recover in less than 20ns from an overdrive condition. Figure 5 shows the CLC1003 in an overdriven condition.

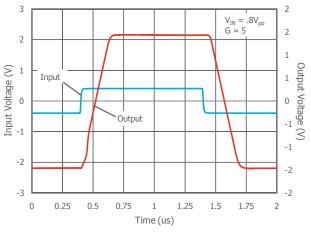
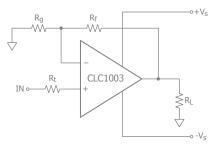


Figure 5. Overdrive Recovery

#### Considerations for Offset and Noise Performance

#### **Offset Analysis**

There are three sources of offset contribution to consider; input bias current, input bias current mismatch, and input offset voltage. The input bias currents are assumed to be equal with and additional offset current in one of the inputs to account for mismatch. The bias currents will not affect the offset as long as the parallel combination of  $R_{\rm f}$  and  $R_{\rm q}$  matches  $R_{\rm t}.$  Refer to Figure 6.



The first place to start is to determine the source resistance. If it is very small an additional resistance may need to be added to keep the values of  $R_f$  and  $R_g$  to practical levels. For this analysis we assume that  $R_t$  is the total resistance present on the non-inverting input. This gives us one equation that we must solve:

$$R_t = Rg||Rf|$$

This equation can be rearranged to solve for R<sub>q</sub>:

$$R_{g} = (R_{t} * R_{f}) / (R_{f} - R_{t})$$

The other consideration is desired gain (G) which is:

$$G = (1 + R_f/R_q)$$

By plugging in the value for  $R_q$  we get

$$R_f = G * R_t$$

And  $R_q$  can be written in terms of  $R_t$  and G as follows:

$$R_{q} = (G * R_{t}) / (G - 1)$$

The complete input offset equation is now only dependent on the voltage offset and input offset terms given by:

$$VI_{OS} = \sqrt{\left(V_{IO}\right)^2 + \left(I_{OS} * RT\right)^2}$$

And the output offset is:

$$VO_{OS} = G * \sqrt{(V_{IO})^2 + (I_{OS} * RT)^2}$$

#### Noise analysis

The complete equivalent noise circuit is shown in Figure 7.

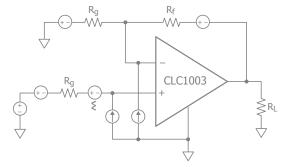


Figure 7: Complete Equivalent Noise Circuit

The complete noise equation is given by:

$$v_{o}^{2} = v_{orext}^{2} + \left(e_{n}\left(1 + \frac{RF}{RG}\right)\right)^{2} + \left(i_{bp} * RT\left(1 + \frac{RF}{RG}\right)\right)^{2} + \left(i_{bn} * RF\right)^{2}$$

Where  $V_{\text{orext}}$  is the noise due to the external resistors and is given by:

$$v_{o}^{2} = \left(e_{n}\left(1 + \frac{RF}{RG}\right)\right)^{2} + \left(e_{G} * \frac{RF}{RG}\right)^{2} + e_{F}^{2}$$

The complete equation can be simplified to:

$$v_{o}^{2} = 3 * (4kT * G * RT) + (e_{n}G)^{2} + 2 * (i_{n} * RT)^{2}$$

It's easy to see that the effect of amplifier voltage noise is proportionate to gain and will tend to dominate at large gains. The other terms will have their greatest impact at large  $R_t$  values at lower gains.

#### Layout Considerations

General layout and supply bypassing play major roles in high frequency performance. CADEKA has evaluation boards to use as a guide for high frequency layout and as aid in device testing and characterization. Follow the steps below as a basis for high frequency layout:

- $\bullet$  Include 6.8µF and 0.1µF ceramic capacitors for power supply decoupling
- Place the  $6.8\mu\text{F}$  capacitor within 0.75 inches of the power pin
- Place the  $0.1\mu\text{F}$  capacitor within 0.1 inches of the power pin
- Remove the ground plane under and around the part, especially near the input and output pins to reduce parasitic capacitance
- Minimize all trace lengths to reduce series inductances

Refer to the evaluation board layouts below for more information.

#### **Evaluation Board Information**

The following evaluation boards are available to aid in the testing and layout of these devices:

Evaluation Board	Products
CEB002	CLC1003 in SOT23-5
CEB003	CLC1003 in SOIC-8

#### **Evaluation Board Schematics**

Evaluation board schematics and layouts are shown in Figures 8-13. These evaluation boards are built for dual- supply operation. Follow these steps to use the board in a single-supply application:

1. Short -Vs to ground.

2. Use C3 and C4, if the  $-V_S$  pin of the amplifier is not directly connected to the ground plane.

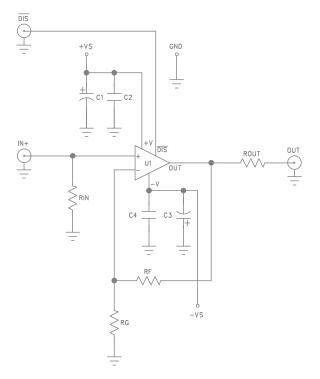


Figure 8. CEB002 Schematic

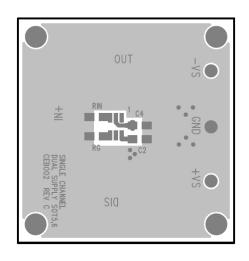


Figure 9. CEB002 Top View

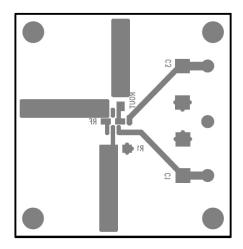


Figure 10. CEB002 Bottom View

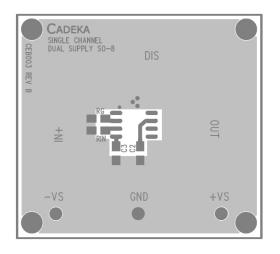


Figure 11. CEB003 Top View

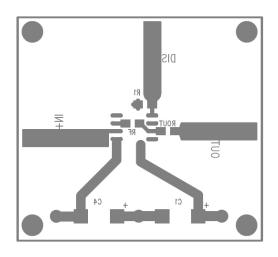
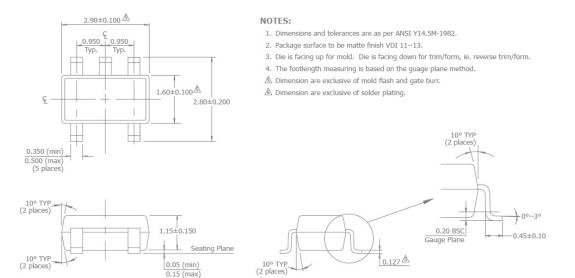


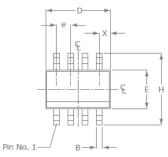
Figure 12. CEB003 Bottom View

#### **Mechanical Dimensions**

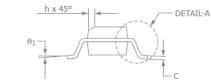
#### SOT23-5 Package



SOIC-8







	SOIC-8	
SYMBOL	MIN	MAX
A1	0.10	0.25
В	0.36	0.48
С	0.19	0.25
D	4.80	4.98
E	3.81	3.99
е	1.27 BSC	
Н	5.80	6.20
h	0.25	0.5
L	0.41	1.27
A	1.37	1.73
θ1	0°	8°
Х	0.55 ref	
θ2	7° BSC	

#### NOTE:

- 1. All dimensions are in millimeters.
- 2. Lead coplanarity should be 0 to 0.1mm (0.004") max.
- 3. Package surface finishing: VDI 24~27
- 4. All dimension excluding mold flashes.
- 5. The lead width, B to be determined at 0.1905mm from the lead tip.

#### For additional information regarding our products, please visit CADEKA at: cadeka.com

A2

#### CADEKA Headquarters Loveland, Colorado

T: 970.663.5452

T: 877.663.5415 (toll free)

A1

CADEKA, the CADEKA logo design, and Comlinear and the Comlinear logo design, are trademarks or registered trademarks of CADEKA Microcircuits LLC. All other brand and product names may be trademarks of their respective companies.

CADEKA reserves the right to make changes to any products and services herein at any time without notice. CADEKA does not assume any responsibility or liability arising out of the application or use of any product or service described herein, except as expressly agreed to in writing by CADEKA; nor does the purchase, lease, or use of a product or service from CADEKA convey a license under any patent rights, copyrights, trademark rights, or any other of the intellectual property rights of CADEKA or of third parties.

